



《风光欣》技术资料

2SD596

NPN EPITAXIAL SILICON TRANSISTOR

Low Collector Saturation Voltage

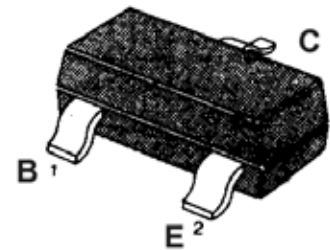
$V_{CE(sat)} = 0.5V(\text{Max.})$ $I_C = 800mA, I_B = 50mA$

Complementary Pair With 2SB624

ABSOLUTE MAXIMUM RATINGS($T_A = 25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter -Base Voltage	V_{EBO}	5	V
Collector Current	I_C	800	mA
Collector Dissipation	P_C	200	mW
Junction Temperature	T_J	150	
Storage Temperature	T_{STG}	-55 ~150	

SOT-23



ELECTRICAL CHARACTERISTICS ($T_A = 25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C = 100 \mu A, I_E = 0$	40			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C = 2mA, I_B = 0$	32			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = 100 \mu A, I_C = 0$	5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 40V, I_E = 0$			100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 6V, I_C = 0$			100	nA
DC Current Gain	H_{FE}	$V_{CE} = 1V, I_C = 150mA$	40	110	400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 50mA$		0.28	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 500mA, I_B = 50mA$		0.98	1.2	V
Transition Frequency	f_T	$V_{CE} = 10V, I_C = 50mA$		190		MHz
Collector Output Capacitance	C_{ob}	$f = 1MHz, V_{CB} = 10V, I_E = 0$		9		pF